# **NEC**

# NPN SILICON TRANSISTOR

## 2SC3616

**DESCRIPTION** 

The 2SC3616 is designed for general-purpose applications

requiring High DC Current Gain.

This is suitable for all kind of driving, instead of Darlington

Transistor, or muting.

**FEATURES** 

• High DC Current Gain.

 $h_{FE}$  = 800 to 3200 (@  $V_{CE}$  = 2.0 V,  $I_{C}$  = 300 mA)

• Low Collector Saturation Voltage.

\*PW ≤ 10 ms, Duty Cycle ≤ 50 %

 $V_{CE(sat)} = 0.14 \text{ V TYP.}$  (@  $I_C/I_B = 300 \text{ mA}/3.0 \text{ mA}$ )

- High V<sub>EBO</sub> : V<sub>EBO</sub>= 15V
- Large Current : I<sub>C(DC)</sub> = 700 mA, I<sub>C(pulse)</sub> = 1.0 A
- High Total Power Dissipation. : P<sub>T</sub> = 0.75 W (T<sub>a</sub> = 25 °C)

### **ABSOLUTE MAXIMUM RATINGS**

# PACKAGE DIMENSIONS in millimeters (inches) 5.2 MAX. XAW COLUMN 1. Emitter 2. Collector JEDEC: TO-92 3. Base IEC: PA33

## ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

| SYMBOL           | CHARACTERISTIC               | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS   |
|------------------|------------------------------|------|------|------|------|---|
| hFE1**           | DC Current Gain              | 800  |      | 3200 | _    | $V_{CE} = 2.0 \text{ V, } I_{C} = 300 \text{ mA}$       |
| hFE2**           | DC Current Gain              | 640  |      |      | -    | $V_{CE} = 2.0 \text{ V, I}_{C} = 500 \text{ mA}$        |
| fT               | Gain Bandwidth Product       | 150  | 250  |      | MHz  | $V_{CE} = 5.0 \text{ V, } I_{E} = -300 \text{ mA}$      |
| Cob              | Output Capacitance           |      | 10   |      | рF   | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$   |
| ІСВО             | Collector Cutoff Current     |      |      | 100  | nΑ   | $V_{CB} = 25 \text{ V, } I_{E} = 0$                     |
| I <sub>EBO</sub> | Emitter Cutoff Current       |      |      | 100  | nΑ   | $V_{EB} = 10 \text{ V, } I_{C} = 0$                     |
| VBE**            | Base to Emitter Voltage      | 600  |      | 700  | mV   | $V_{CE} = 2.0 \text{ V, I}_{C} = 50 \text{ mA}$         |
| VCE(sat)**       | Collector Saturation Voltage |      | 0.14 | 0.3  | V    | $I_C = 300 \text{ mA}, I_B = 3.0 \text{ mA}$            |
| VBE(sat)**       | Base Saturation Voltage      |      | 0.77 | 1.2  | ٧    | $I_C = 300 \text{ mA}, I_B = 3.0 \text{ mA}$            |
| ton              | Turn-On Time                 |      | 0.13 |      | μs   | $/ V_{CC} = 10 \text{ V}, V_{BE(off)} = -2.7 \text{ V}$ |
| t <sub>stg</sub> | Storage Time                 |      | 0.90 |      | μs   | I <sub>C</sub> = 200 mA                                 |
| <sup>t</sup> off | Turn-Off Time                |      | 1.1  |      | μs   | $I_{B1} = -I_{B2} = 4.0 \text{ mA}$                     |

<sup>\*\*</sup>Pulsed PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

## Classification of h<sub>FE1</sub>

| Rank  | M           | L            | К            |
|-------|-------------|--------------|--------------|
| Range | 800 to 1600 | 1200 to 2400 | 2000 to 3200 |

Test Conditions:  $V_{CE} = 2.0 \text{ V}$ ,  $I_{C} = 300 \text{ mA}$ 

## TYPICAL CHARACTERISTICS (Ta = 25 °C)



















